

AVIONICS PULSED POWER TRANSISTOR

500 WATTS, 960-1215 MHz, 10us PULSE, 10% DUTY

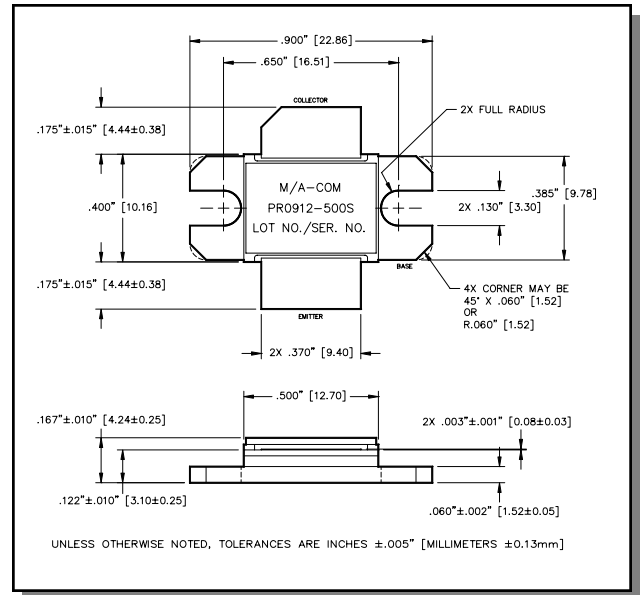
MAPR-000912-500S00

11 Jan 2007

Features

- NPN Silicon Microwave Power Transistors
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Inter digitized Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metallization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package
- RoHS Compliant

Outline Drawing



Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	80	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	I_C	52.5	A
Power Dissipation @ +25°C	P_{TOT}	2.2	kW
Storage Temperature	T_{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Electrical Specifications: $T_C = 25 \pm 5^\circ\text{C}$ (ROOM AMBIENT)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	$I_C = 80\text{mA}$		BV_{CES}	80	-	V
Collector-Emitter Leakage Current	$V_{CE} = 40\text{V}$		I_{CES}	-	15	mA
Thermal Resistance	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960, 1090, 1215 MHz	$R_{TH(JC)}$	-	0.08	°C/W
Output Power	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960, 1090, 1215 MHz	P_O	500	-	W
Power Gain	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960, 1090, 1215 MHz	G_P	9.0	-	dB
Collector Efficiency	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960, 1090, 1215 MHz	η_C	45	-	%
Input Return Loss	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960, 1090, 1215 MHz	RL	-	-9	dB
Load Mismatch Tolerance	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960 MHz	VSWR-T	-	3:1	-
Load Mismatch Stability	$V_{CC} = 50\text{V}$, $P_{in} = 63\text{W}$	F = 960, 1090, 1215 MHz	VSWR-S	-	1.5:1	-

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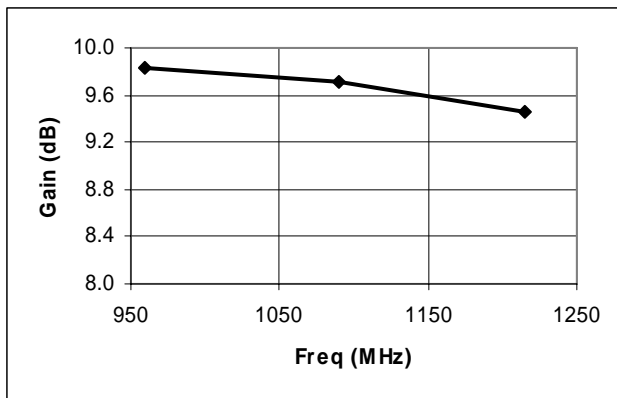
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Typical RF Performance

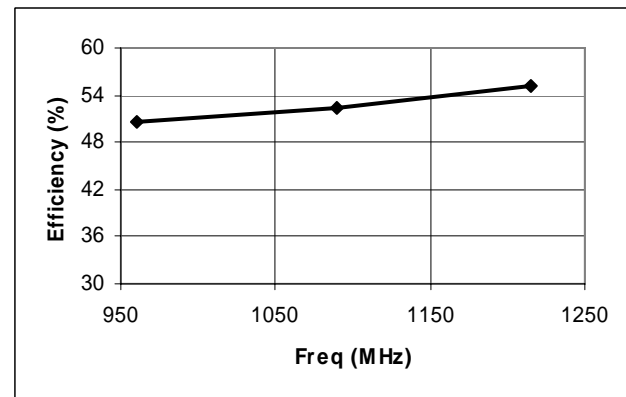
Freq. (MHz)	Pin (W)	Pout (W)	Gain (dB)	Δ Gain (dB)	Ic (A)	Eff (%)	RL (dB)	VSWR-S (1.5:1)	VSWR-T (3:1)	P1dB Overdrive	
										Pout	Δ Po
960	63	598	9.77	-	23.5	50.9	-17.1	S	P	675	0.52
1090	63	582	9.65	-	21.9	53.1	-21.8	S	-	677	0.66
1215	63	554	9.44	0.33	19.7	56.1	-16.8	S	-	619	0.48

Note: Δ Po(dB) is the difference between Pout at 1dB overdrive and Pout at Pin = 63W.

Gain vs. Frequency



Collector Efficiency vs. Frequency

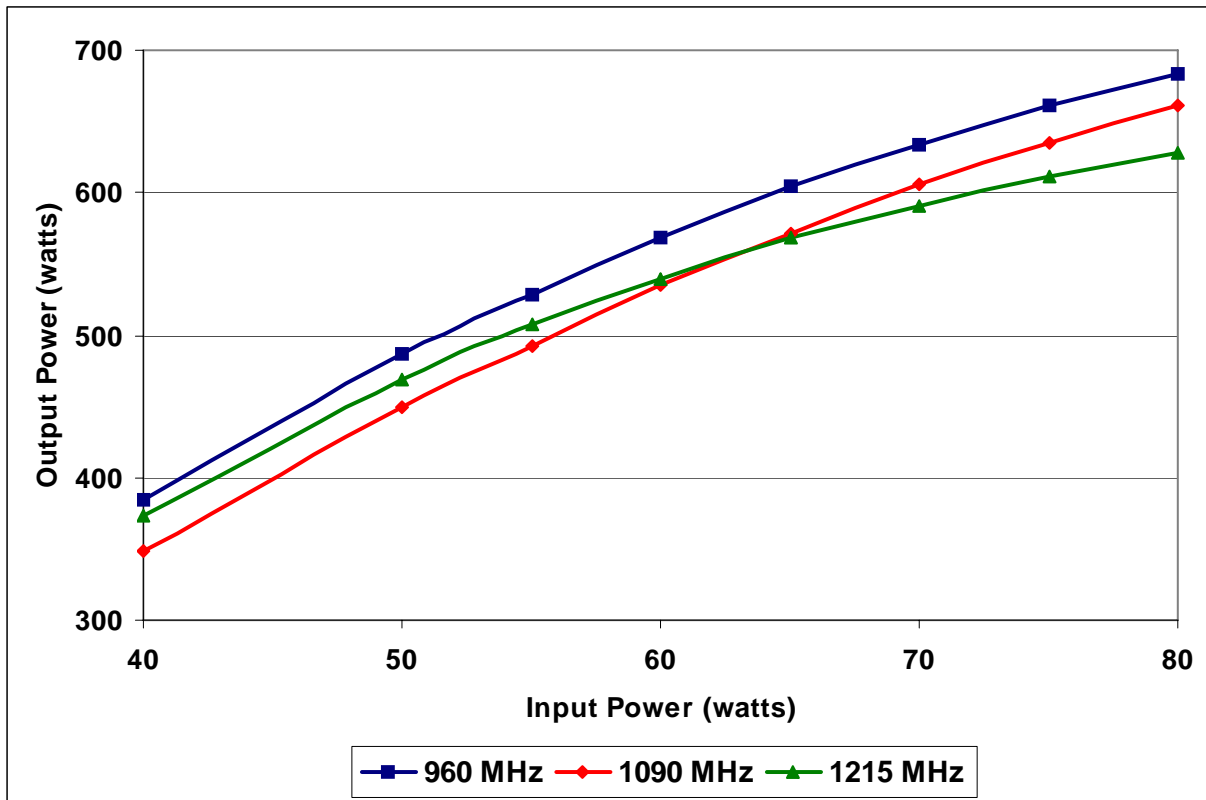


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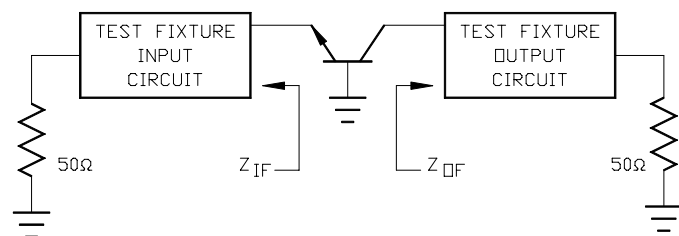
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RF Power Transfer Curve
(Output Power Vs. Input Power)



Broadband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
960	1.3 - j1.4	1.2 - j1.4
1025	1.3 - j1.1	1.2 - j1.1
1090	1.2 - j0.9	1.3 - j0.9
1150	1.2 - j0.8	1.4 - j0.7
1215	1.0 - j0.8	1.3 - j0.6

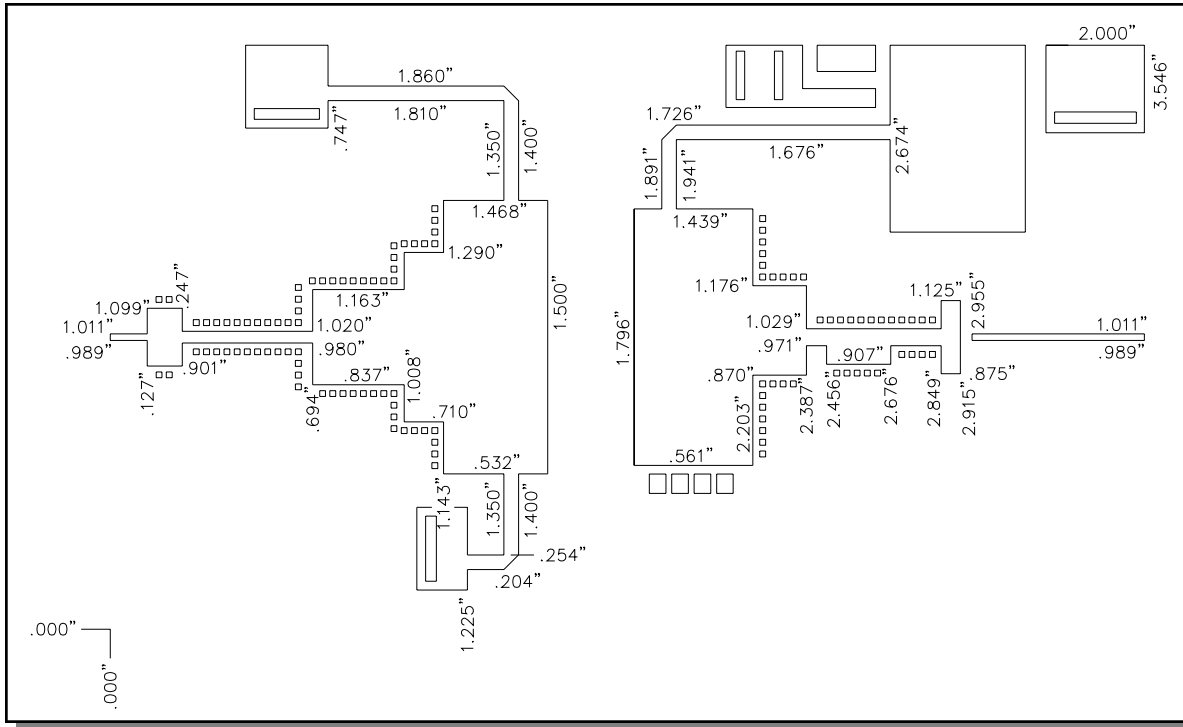


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Test Fixture Circuit Dimensions



Test Fixture Assembly

